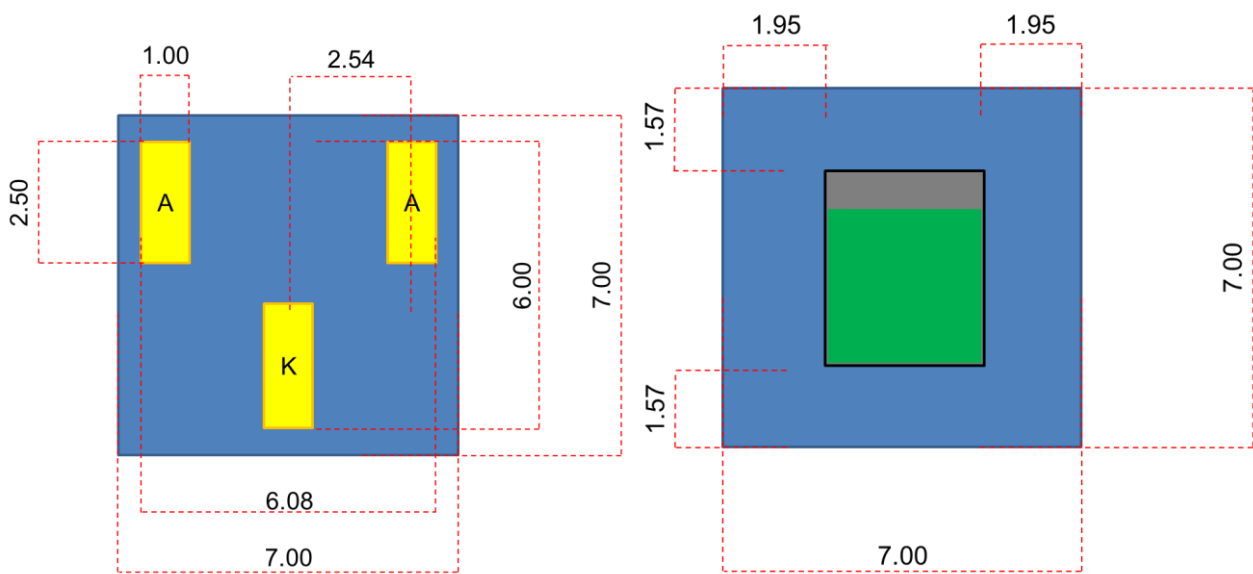


SiPM SAMPLES	type: FBK SiPM NUV-HD-RH	Sample num.: 3 (#2, #3, #4)
	Package: 1ch	Deliv. date: August, 2021

SiPM parameters:

Breakdown Voltage (at RoomT)	~33.0 V		
Active Area (nominal)	3.0x3.0 mm ²	Device Type	NUV-HD-RH
Cell pitch	15 μm	Junction type	p-on-n

Package details:



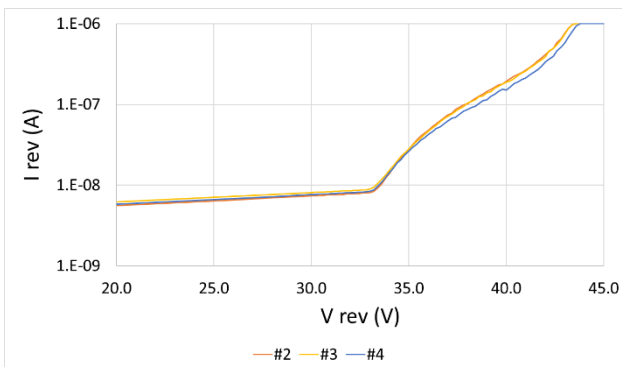
Bottom view

Front view:

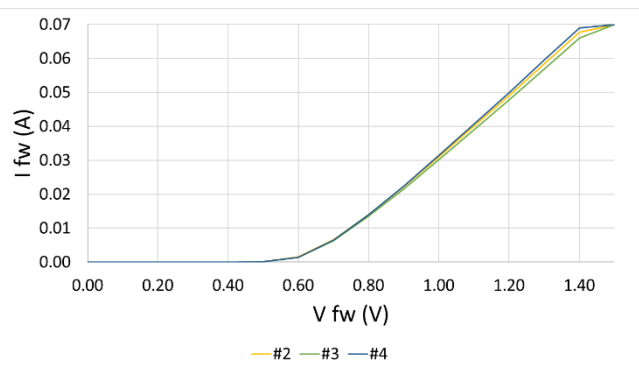
Die size (black rectangle) 3.10x3.85 mm²

Active area (green square) 3.0x3.0 mm²

Reverse bias IV at room temperature:



Forward bias IV at room temperature:

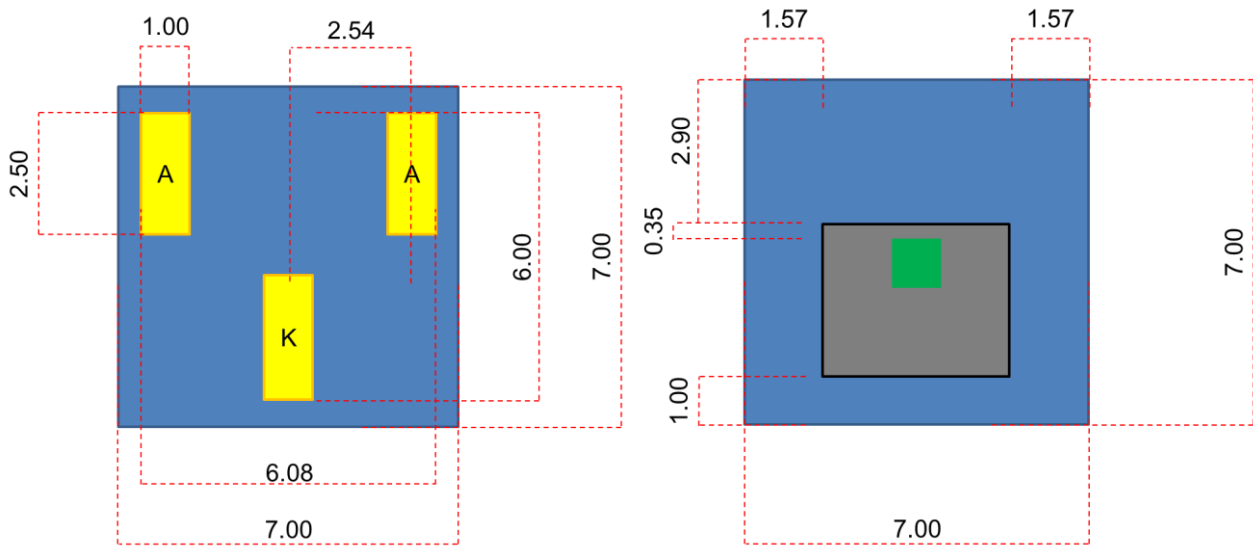


SiPM SAMPLES	type: FBK SiPM NUV-HD-RH	Sample num.: 4 (#5, #6, #7, #8)
	Package: 1ch	Deliv. date: August, 2021

SiPM parameters:

Breakdown Voltage (at RoomT)	~33.0 V		
Active Area (nominal)	1.0x1.0 mm ²	Device Type	NUV-HD-RH
Cell pitch	15 μm	Junction type	p-on-n

Package details:



Bottom view

Front view:

Die size (black rectangle) 3.85x3.10 mm²

Active area (green square) 1.0x1.0 mm²

Reverse bias IV at room temperature:

Forward bias IV at room temperature:

